

# Transient Voltage Suppressors for ESD Protection

### **General Description**

The FTV5.0UE is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

### Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

### Features

- Small Body Outline Dimensions
- Low Body Height
- Stand-off Voltage: 2.5 V 7.0 V
- Peak Power up to 200 Watts @ 8 x 20 \_s Pulse
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection
- We declare that the material of product compliance with RoHS requirements.

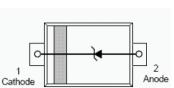
### Absolute Ratings (T<sub>amb</sub>=25°C)

Symbol	Parameter	Value	Units
P <sub>PP</sub>	Peak Pulse Power (t <sub>P</sub> = 8/20µs)	200	W
TL	Maximum lead temperature for soldering during 10s	260	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>op</sub>	Operating Temperature Range	-40 to +125	°C
Tj	Maximum junction temperature	150	°C
	IEC61000-4-2 (ESD) air discharge contact discharge	土15 土8	KV
	IEC61000-4-4 (EFT)	40	А
	ESD Voltage Per Human Body Model	16	KV

**First Silicon** 

#### ORDERING INFORMATION

Device	Package	Shipping		
FTV05UE	SOD-523	3000/Tape & Reel		

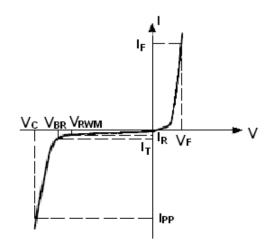


SOD-523

# FTV05UE

### **Electrical Parameter**

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ I <sub>PP</sub>
$V_{RWM}$	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ $V_{\text{RWM}}$
Ι <sub>Τ</sub>	Test Current
$V_{BR}$	Breakdown Voltage @ $I_T$
I <sub>F</sub>	Forward Current
$V_{F}$	Forward Voltage @ I <sub>F</sub>



Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.VF = 0.9V at IF = 10mA

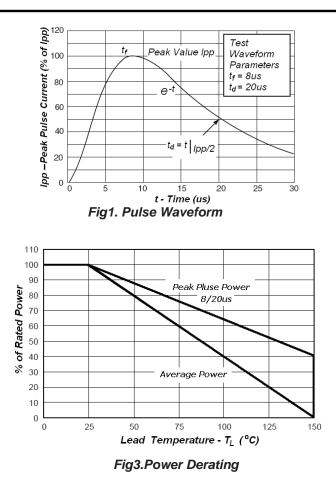
Device	Device	V <sub>RWM</sub> (V)	I <sub>R</sub> (uA) @ V <sub>RWM</sub>	V <sub>BR</sub> (V)@ I <sub>T</sub> (Note 1)	Ι <sub>τ</sub>	V <sub>c</sub> (V) @ I <sub>PP</sub> =5 A*	V <sub>c</sub> (V) @ Max I <sub>PP</sub> *	І <sub>РР</sub> (А)*	Р <sub>РК</sub> (W)*	C (pF)
	Marking	Мах	Max	Min	mA	Тур	Max	Max	Мах	Тур
FTV2.5UE	ZD	2.5	6.0	4.0	1.0	6.5	10.9	11.0	120	145
FTV3.3UE	ZE	3.3	1.0	5.0	1.0	8.4	14.1	11.2	158	105
FTV05UE	ZF	5.0	1.0	6.2	1.0	11.6	18.6	9.4	174	80
FTV06UE	ZG	6.0	1.0	6.8	1.0	12.4	20.5	8.8	181	70
FTV07UE	ZH	7.0	1.0	7.5	1.0	13.5	22.7	8.8	200	65
FTV12UE	ZM	12	1.0	13.5	1.0	17	25	9.6	240	55

\*Surge current waveform per Figure 1.

1.  $V_{BR}$  is measured with a pluse test current  $I_T$  at an ambient temperature of  $25^\circ\!\mathbb{C}$  .



## **FTV05UE**



#### **Application Note**

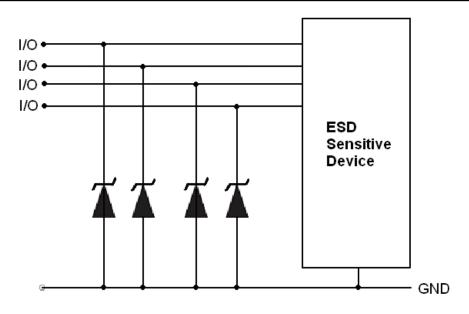
Electrostatic discharge (ESD) is a major cause of failure in electronic systems. Transient Voltage Suppressors (TVS) are an ideal choice for ESD protection. They are capable of clamping the incoming transient to a low enough level such that damage to the protected semiconductor is prevented.

Surface mount TVS offer the best choice for minimal lead inductance. They serve as parallel protection elements, connected between the signal line to ground. As the transient rises above the operating voltage of the device, the TVS becomes a low impedance path diverting the transient current to ground. The FTV5.0UE is the ideal board evel protection of ESD sensitive semiconductor components.

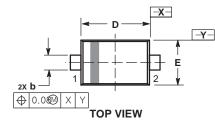
The tiny SOD523 package allows design flexibility in the design of high density boards where the space saving is at a premium. This enables to shorten the routing and contributes to hardening againt ESD.

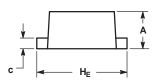


## **FTV05UE**



SC-79/SOD-523





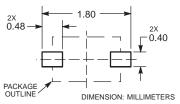
SIDE VIEW

NOTES:

- DIES:
  DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- BASE MATERIAL.
- DIMENSIONS OF AND E DO NOT INCLUDE MOLD FLASH, PRO-TRUSIONS, OR GATE BURRS.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.50	0.60	0.70		
b	0.25	0.30	0.35		
с	0.07	0.14	0.20		
D	1.10	1.20	1.30		
E	0.70	0.80	0.90		
HE	1.50	1.60	1.70		
L	0.30 REF				
L2	0.15	0.20	0.25		

RECOMMENDED SOLDERING FOOTPRINT\*



**First Silicon**